

T-03-17

Features

- Ultrafast with Soft Recovery Characteristic ($t_{rr} < 100ns$)
- +175°C Rated Junction Temperature
- Reverse Voltage Up to 1000V
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supply
- Power Switching Circuits
- General Purpose

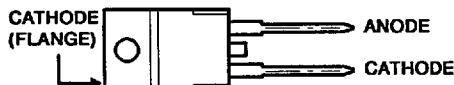
Description

RUR1570, RUR1580, RUR1590, RUR15100 are ultrafast diodes with soft recovery characteristics ($t_{rr} < 100ns$). They have a low forward voltage drop and are silicon nitride passivated, ion-implanted, epitaxial construction.

These devices are intended for use as flywheel/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast recovery with soft recovery characteristics minimizes ringing and electrical noise in many power switching circuits thus reducing power loss in the switching transistor.

All are supplied in TO-220AC packages.

Package

 TO-220AC
TOP VIEW

Symbol

Absolute Maximum Ratings ($T_C = +25^\circ C$)

	RUR1570	RUR1580	RUR1590	RUR15100
Peak Repetitive Reverse Voltage	V _{RRM} 700V	800V	900V	1000V
Working Peak Reverse Voltage	V _{RWM} 700V	800V	900V	1000V
DC Blocking Voltage	V _R 700V	800V	900V	1000V
Average Rectified Forward Current	I _{F(AV)} 15A	15A	15A	15A
($T_C = +141.25^\circ C$)				
Peak Forward Repetitive Current	I _{FRM} 30A	30A	30A	30A
(Square wave 20kHz)				
Nonrepetitive Peak Surge Current	I _{FSM} 200A	200A	200A	200A
(Surge applied at rated load condition halfwave 1phase 60Hz)				
Maximum Power Dissipation	P _D 100W	100W	100W	100W
Operating and Storage Temperature	T _{STG, TJ} -65°C to +175°C	-65°C to +175°C	-65°C to +175°C	-65°C to +175°C

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 ULTRA-FAST
RECTIFIERS

Specifications RUR1570, RUR1580, RUR1590, RUR15100

HARRIS SEMICOND SECTOR

56E D

■ 4302271 0042387 145 ■ HAS

Electrical Characteristics ($T_C = +25^\circ\text{C}$) unless Otherwise Specified.

T-03-17

SYMBOL	TEST CONDITION	LIMITS												UNITS	
		RUR1570			RUR1580			RUR1590			RUR15100				
		MIN	Typ	MAX	MIN	Typ	MAX	MIN	Typ	MAX	MIN	Typ	MAX		
V_F	$I_F = 15\text{A}$ $T_C = +150^\circ\text{C}$	-	-	1.50	-	-	1.50	-	-	1.50	-	-	1.50	V	
	$I_F = 15\text{A}$ $T_C = +25^\circ\text{C}$	-	-	1.80	-	-	1.80	-	-	1.80	-	-	1.80	V	
$I_R @ T_C = +150^\circ\text{C}$	$V_R = 700\text{V}$	-	-	500	-	-	-	-	-	-	-	-	-	μA	
	$V_R = 800\text{V}$	-	-	-	-	-	500	-	-	-	-	-	-	μA	
	$V_R = 900\text{V}$	-	-	-	-	-	-	-	-	500	-	-	-	μA	
	$V_R = 1000\text{V}$	-	-	-	-	-	-	-	-	-	-	-	500	μA	
$I_R @ T_C = +25^\circ\text{C}$	$V_R = 700\text{V}$	-	-	100	-	-	-	-	-	-	-	-	-	μA	
	$V_R = 800\text{V}$	-	-	-	-	-	100	-	-	-	-	-	-	μA	
	$V_R = 900\text{V}$	-	-	-	-	-	-	-	-	100	-	-	-	μA	
	$V_R = 1000\text{V}$	-	-	-	-	-	-	-	-	-	-	-	100	μA	
t_{rr}	$I_F = 1\text{A}$	-	-	100	-	-	100	-	-	100	-	-	100	ns	
	$I_F = 15\text{A}$	-	-	125	-	-	125	-	-	125	-	-	125	ns	
t_a	$I_F = 15\text{A}$	-	75	-	-	75	-	-	75	-	-	75	-	ns	
t_b	$I_F = 15\text{A}$	-	40	-	-	40	-	-	40	-	-	40	-	ns	
$R_{\Theta JC}$		-	-	1.5	-	-	1.5	-	-	1.5	-	-	1.5	$^\circ\text{C/W}$	
W_{avl}		-	-	20	-	-	20	-	-	20	-	-	20	mJ	

Definitions

V_F = Instantaneous forward voltage ($pw = 300\mu\text{s}$, $D = 2\%$).

I_R = Instantaneous reverse current ($pw = 300\mu\text{s}$, $D = 2\%$).

t_{rr} = Reverse recovery time at $dI_F/dt = 100\text{A}/\mu\text{s}$, summation of $t_a + t_b$.

t_a = Time to reach peak reverse current at $dI_F/dt = 100\text{A}/\mu\text{s}$ (See Figure 2).

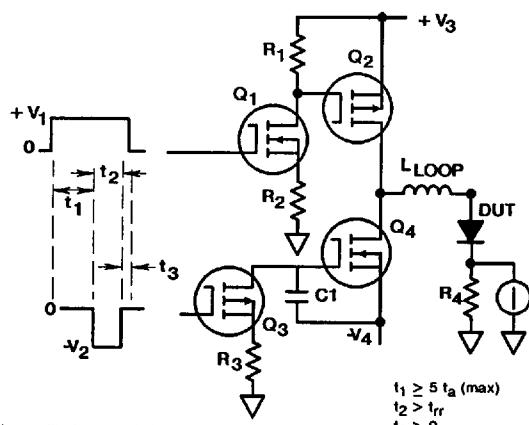
t_b = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} . (See Figure 2)

$R_{\Theta JC}$ = Thermal resistance junction to case.

W_{avl} = Controlled avalanche energy (See Figures 7 & 8).

pw = pulse width.

D = duty cycle.



V_1 amplitude controls I_F
 V_2 amplitude controls dI/dt
 L_1 = self inductance of R_4

FIGURE 1. t_{rr} TEST CIRCUIT

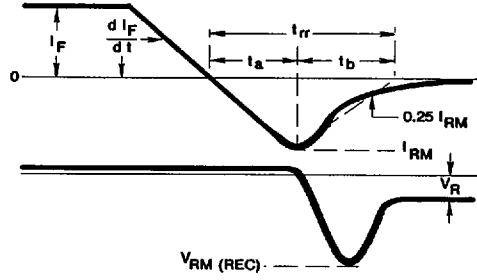


FIGURE 2. DEFINITIONS OF t_{rr} , t_a AND t_b

HARRIS SEMICOND SECTOR

56E D ■ 4302271 0042388 081 ■ HAS

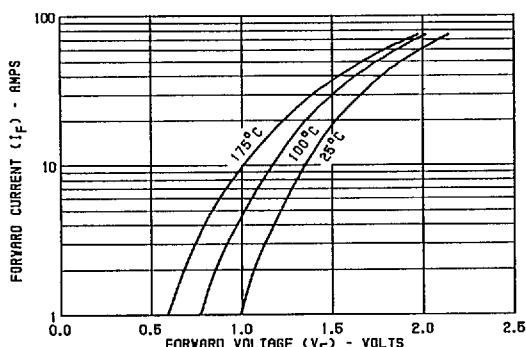


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

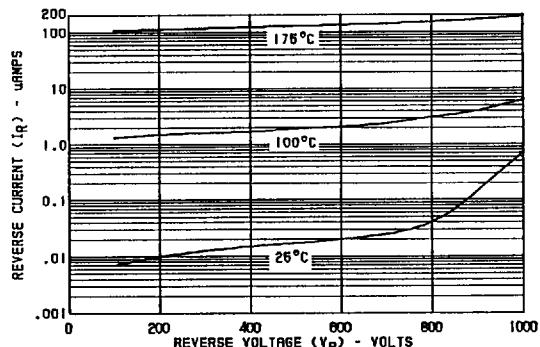


FIGURE 4. TYPICAL REVERSE CURRENT vs VOLTAGE

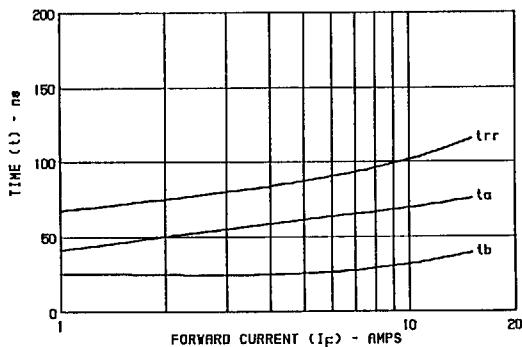


FIGURE 5. TYPICAL t_rr, t_a AND t_b CURVES vs FORWARD CURRENT

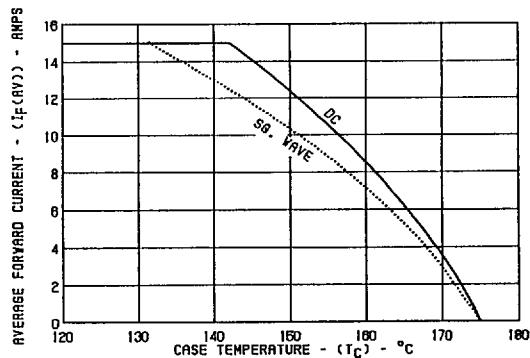


FIGURE 6. CURRENT DERATING CURVE FOR ALL TYPES

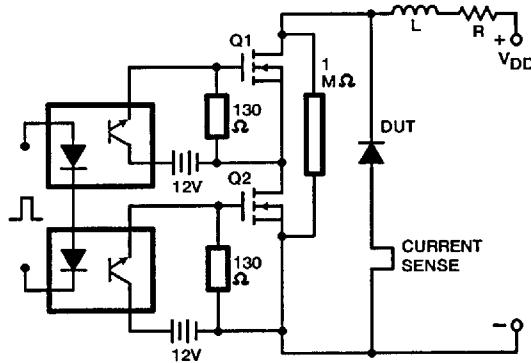


FIGURE 7. AVALANCHE ENERGY TEST CIRCUIT

$$I_L \text{peak} = 1A, L = 40mH, R < 0.1\Omega, W_{avl} = (1/2) L I^2 [V_{avl}/(V_{avl}-V_{dd})]$$

Q1 and Q2 are 1000V MOSFETs

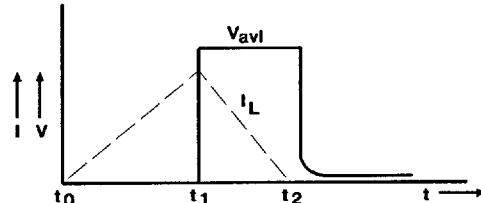


FIGURE 8. AVALANCHE CURRENT & VOLTAGE WAVEFORM

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ULTRA-FAST
RECTIFIERS